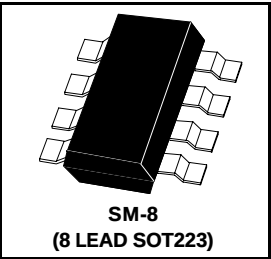
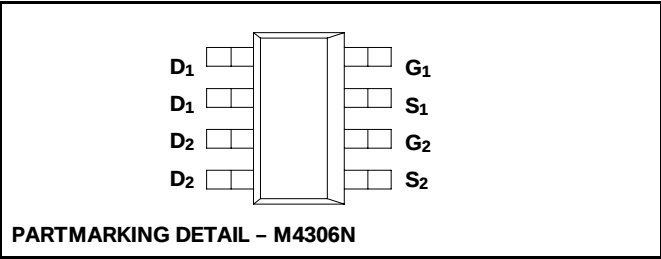


SM-8 DUAL N-CANNEL ENHANCEMENT
MODE MOSFETS

ISSUE 1 - NOVEMBER 1995

ZDM4306N



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	2	A
Pulsed Drain Current	I_{DM}	15	A
Gate-Source Voltage	V_{GS}	± 20	V
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^{\circ}C$ * Any single die "on" Both die "on" equally	P_{tot}	2.5 3.0	W W
Derate above $25^{\circ}C$ * Any single die "on" Both die "on" equally		20 24	mW/ $^{\circ}C$ mW/ $^{\circ}C$
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		50.0 41.6	$^{\circ}C/W$ $^{\circ}C/W$

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

Note:

This data is derived from development material and does not necessarily mean that the device will go into production

ZDM4306N

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

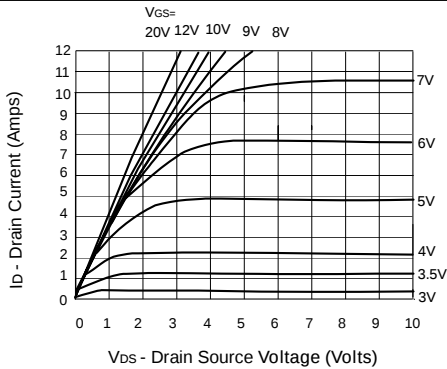
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60			V	$I_D=1\text{mA}$, $V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.3		3	V	$I_D=1\text{mA}$, $V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			10 100	μA μA	$V_{DS}=60\text{V}$, $V_{GS}=0$ $V_{DS}=48\text{V}$, $V_{GS}=0\text{V}$, $T=125^{\circ}\text{C}(2)$
On-State Drain Current(1)	$I_{D(on)}$	12			A	$V_{DS}=10\text{V}$, $V_{GS}=10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		0.22 0.32	0.33 0.45	Ω Ω	$V_{GS}=10\text{V}$, $I_D=3\text{A}$ $V_{GS}=5\text{V}$, $I_D=1.5\text{A}$
Forward Transconductance (1)(2)	g_{fs}	700			mS	$V_{DS}=25\text{V}$, $I_D=3\text{A}$
Input Capacitance (2)	C_{iss}			350	pF	$V_{DS}=25\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$
Common Source Output Capacitance (2)	C_{oss}			140	pF	
Reverse Transfer Capacitance (2)	C_{rss}			30	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$			8	ns	$V_{DD}\approx 25\text{V}$, $V_{GEN}=10\text{V}$, $I_D=3\text{A}$
Rise Time (2)(3)	t_r			25	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$			30	ns	
Fall Time (2)(3)	t_f			16	ns	

1) Measured under pulsed conditions. Width=300 μs . Duty cycle $\leq 2\%$

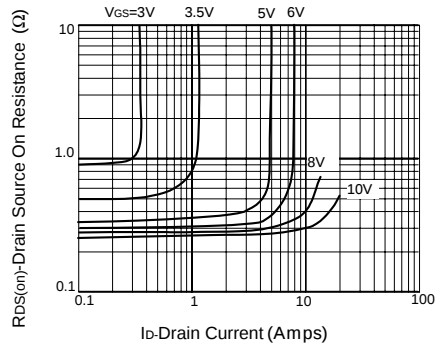
(2) Sample test.

(3) Switching times measured with 50 Ω source impedance and <5ns rise time on a pulse generator

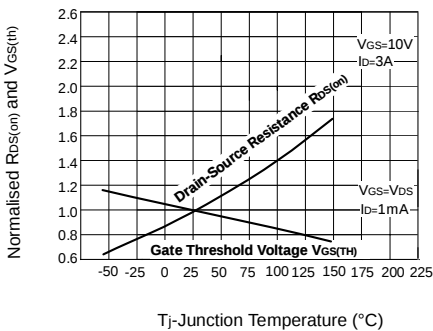
TYPICAL CHARACTERISTICS



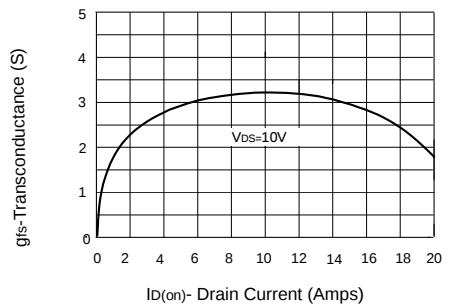
Saturation Characteristics



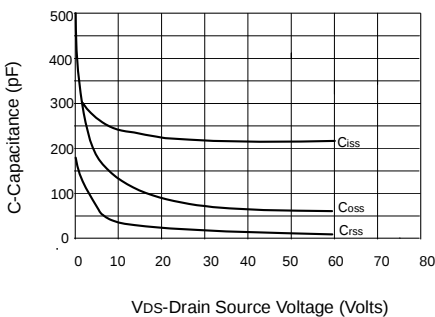
On-resistance v drain current



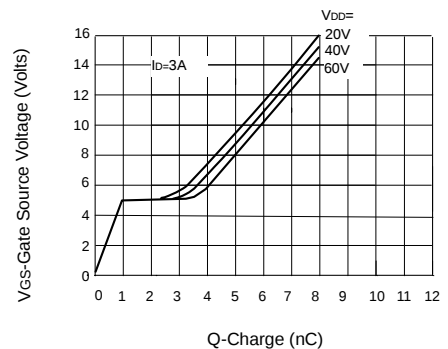
Normalised $R_{DS(on)}$ and $V_{GS(th)}$ v Temperature



Transconductance v drain current



Capacitance v drain-source voltage



Gate charge v gate-source voltage